

Mass separated Focused Ion Beams using Alloy Liquid Metal Ion Sources

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Outline

Introduction

Alloy LMIS
Preparation
Characterisation

FIB System IMSA-100

Applications
CoSi₂ microstructures
Ge⁺, Co⁺⁺ beams - damage & annealing
Sputtering investigations
Micro-optical applications
Ion-acoustic Microscopy

SUMMARY

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Alloy LMIS

Preparation:

Needed ion species → choose a suited alloy
- sufficient concentration (phase diagram)
- low melting temperature (eutectic alloy)
- low vapour pressure at T_{melt}
- no chemically related effects

Preparation of the needle - hair pin or capillary type
- spot welding of the source base
- electro-chemical etching of the W-tip ($r_{tip} \sim 5 \mu m$)
- mechanical treatment Ta-tip
- wetting by dipping in a crucible in HV

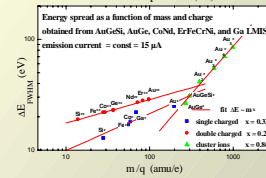
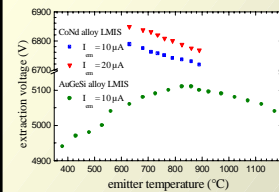
Test and analysis:

- I-V-characteristics
- long-term stability
- temperature behaviour
- mass spectra
- energy distribution and ballistic deficit (energy spread)
- axial angular intensity

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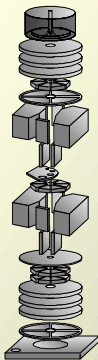
Results



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FIB system IMSA - 100



alloy LMIS
objective lens
stigmator 1
measuring aperture
E x B 1
beam blanking 1
variable aperture
stigmator 2
E x B 2
beam blanking 2
blanking aperture
deflection system
projective lens
MCP detector
xy stage

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Parameter IMSA-100 FZ Rossendorf:

Energy: 20 - 50 keV (single charged)
Ions: B, Si, Cr, Fe, Co, Ni, Ga, Ge, Nd, Er, Au, ...
Current: 0.01 - 30 nA (max. 10 A/cm² at 100 nm spot)
Spot size: 100 - 2000 nm
Sample: 6" - wafer, 7" - masks
Stage: Laser-interferometer controlled, x-y-area: 160 x 160 mm² accuracy: 50 nm
Options: Heating targets up to 700 °C
Cooling, $\varnothing T = 60$ grd
Sample contacting, rotating
Acoustic sensor
ASCII, AutoCAD data input

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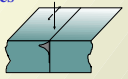
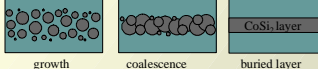


Applications

CoSi₂ microstructures

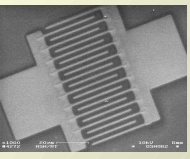
Co²⁺FIB 70 keV

Writing FIB
Co-implantation
into a heated target

growth nucleation
coalescence Ostwald ripening
annealing 600°C, 60 min and 1000°C, 30 min in N₂ →

buried layer

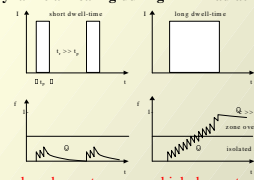


SEM image of a MSM-Photodetector teststructure on silicon with CoSi₂ electrodes

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Ge⁺⁺ and Co⁺⁺ implantation as a function of T

Investigation of damage accumulation and dynamic annealing during FIB irradiation



low dose rate averaged
isolated amorphous zones can anneal
Si crystalline

high dose rate within the FIB
overlap of amorphous zones can not anneal
Si amorphous

$t_d = 1 \mu s, I = 0.7 nA$
 $J = 1.4 \times 10^{15} \text{ ions/cm}^2 \text{ s}$
 $j = 44 \mu A/cm^2$

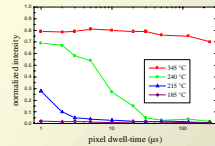
$t_d = 250 \mu s, I = 0.7 nA$
 $J = 3 \times 10^{18} \text{ ions/cm}^2 \text{ s}$
 $j = 1 A/cm^2$

f - normalized damage fraction, 0 = crystalline; 1 = amorphous
⊖ - temperature depending annealing time constant

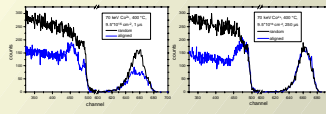
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Results:

70 keV Ge⁺⁺, dose: $1.3 \times 10^{15} \text{ ions/cm}^2$



Normalized intensity of the Raman line of c-Si of 520 cm^{-1} as a function of the pixel dwell-time for different temperatures.



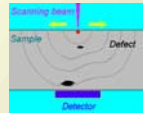
RBS-C analysis after 70 keV Co⁺⁺ implantation for short (left) and long (right) dwell-times.

The relaxation-time lies in the μs -range.

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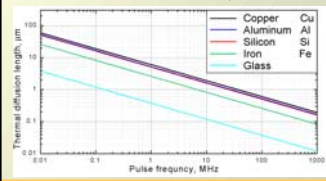
Ion - acoustic Microscopy

Principle:
modulated particle beam generates thermoelastic waves



Resolution:
 $d^2 = d_h^2 + d_s^2 + d_v^2$

Thermal diffusion length $d_h = \sqrt{\frac{\kappa}{\pi C \rho f}}$



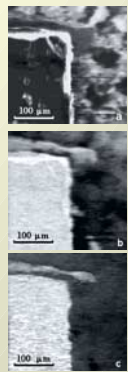
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Results

Secondary electron (a), acoustic amplitude (b) and acoustic phase (c) images of a corner of a silicon chip glued on a brass plate.

Pictures size is 100x100 pixels.
Acoustic images resolution is about 15 μm .
SE image resolution is 3 μm .
Exposition time of the acoustic images was 40 minutes.

Au⁺ ion beam.
E = 35 keV I = 2.6 nA



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Summary

- The use of mass separated FIB from alloy LMIS offers many new applications in micro-structuring.
- The obtainable spot size is determined by the energy spread (I_{rms}, q, m, T) and on the influence of the E x B filter.
- The variability of the dose rate can be used for basic damage investigations in a range which is not possible with other techniques.
- The writing implantation with FIB is very useful in maskless structuring of prototypes within the R&D process.

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